

## P-channel 40 V, 0.0175 $\Omega$ typ., 8 A, STripFET™ F6 Power MOSFET in a PowerFLAT™ 3.3 x 3.3 package

Datasheet - production data

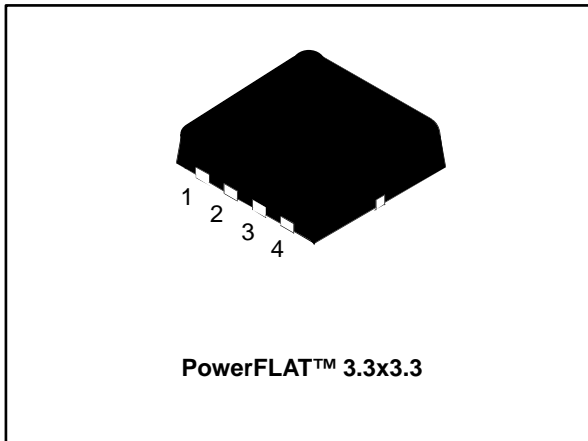


Figure 1: Internal schematic diagram

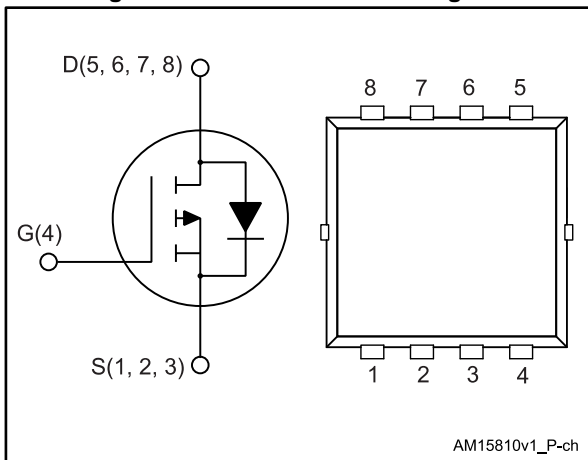


Table 1: Device summary

Order code	Marking	Package	Packaging
STL8P4LLF6	8P4F6	PowerFLAT™ 3.3 x 3.3	Tape and reel

### Features

Order code	V <sub>DS</sub>	R <sub>DS(on)</sub> max.	I <sub>D</sub>	P <sub>TOT</sub>
STL8P4LLF6	40 V	0.0205 $\Omega$	8 A	2.9 W

- Very low on-resistance
- Very low gate charge
- High avalanche ruggedness
- Low gate drive power loss

### Applications

- Switching applications

### Description

This device is a P-channel Power MOSFET developed using the STripFET™ F6 technology, with a new trench gate structure. The resulting Power MOSFET exhibits very low R<sub>DS(on)</sub> in all packages.

- For the P-channel Power MOSFET, current polarity of voltages and current have to be reversed.

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# 1 Electrical ratings

**Table 2: Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{DS}$	Drain-source voltage	40	V
$V_{GS}$	Gate-source voltage	$\pm 20$	V
$I_D^{(1)}$	Drain current (continuous) at $T_{pcb} = 25\text{ }^\circ\text{C}$	8	A
$I_D^{(1)}$	Drain current (continuous) at $T_{pcb} = 100\text{ }^\circ\text{C}$	5	A
$I_{DM}^{(1)(2)}$	Drain current (pulsed)	32	A
$P_{TOT}$	Total dissipation at $T_{pcb} = 25\text{ }^\circ\text{C}$	2.9	W
$T_{stg}$	Storage temperature	-55 to 150	$^\circ\text{C}$
$T_j$	Maximum junction temperature	150	$^\circ\text{C}$

**Notes:**

<sup>(1)</sup>this value is related to  $R_{thj-pcb}$

<sup>(2)</sup>Pulse width limited by safe operating area.

**Table 3: Thermal data**

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case max	2.50	$^\circ\text{C/W}$
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-pcb max.	42.8	$^\circ\text{C/W}$

**Notes:**

<sup>(1)</sup>When mounted on FR-4 board of 1 inch<sup>2</sup>, 2oz Cu,  $t \leq 10\text{ s}$



For the P-channel Power MOSFET, current polarity of voltages and current have to be reversed.

## 2 Electrical characteristics

( $T_C = 25\text{ °C}$  unless otherwise specified)

**Table 4: Static**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0\text{ V}$ , $I_D = 250\text{ }\mu\text{A}$	40			V
$I_{DSS}$	Zero gate voltage Drain current	$V_{GS} = 0\text{ V}$ , $V_{DS} = 40\text{ V}$			1	$\mu\text{A}$
		$V_{GS} = 0\text{ V}$ , $V_{DS} = 40\text{ V}$ , $T_C = 125\text{ °C}$			10	$\mu\text{A}$
$I_{GSS}$	Gate-body leakage current	$V_{DS} = 0\text{ V}$ , $V_{GS} = \pm 20\text{ V}$			$\pm 100$	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$ , $I_D = 250\text{ }\mu\text{A}$	1		2.5	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}$ , $I_D = 4\text{ A}$		0.0175	0.0205	$\Omega$
		$V_{GS} = 4.5\text{ V}$ , $I_D = 4\text{ A}$		0.021	0.029	

**Table 5: Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{ISS}$	Input capacitance	$V_{DS} = 25\text{ V}$ , $f = 1\text{ MHz}$ , $V_{GS} = 0\text{ V}$	-	2850	-	pF
$C_{OSS}$	Output capacitance		-	270	-	pF
$C_{RSS}$	Reverse transfer capacitance		-	180	-	pF
$Q_g$	Total gate charge	$V_{DD} = 20\text{ V}$ , $I_D = 8\text{ A}$ , $V_{GS} = 4.5\text{ V}$ (see <a href="#">Figure 14: "Gate charge test circuit"</a> )	-	22	-	nC
$Q_{gs}$	Gate-source charge		-	9.4	-	nC
$Q_{gd}$	Gate-drain charge		-	7.3	-	nC
$R_G$	Gate input resistance	$I_D = 0\text{ A}$ , gate DC bias = $0\text{ V}$ , $f = 1\text{ MHz}$ , magnitude of alternative signal = $20\text{ mV}$	-	1.4	-	$\Omega$

**Table 6: Switching times**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 20\text{ V}$ , $I_D = 4\text{ A}$ $R_G = 4.7\text{ }\Omega$ , $V_{GS} = 10\text{ V}$ (see <a href="#">Figure 13: "Switching times test circuit for resistive load"</a> )	-	43	-	ns
$t_r$	Rise time		-	47	-	ns
$t_{d(off)}$	Turn-off-delay time		-	148	-	ns
$t_f$	Fall time		-	19	-	ns



For the P-channel Power MOSFET, current polarity of voltages and current have to be reversed.

Table 7: Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{SD}^{(1)}$	Forward on voltage	$V_{GS} = 0 \text{ V}$ , $I_{SD} = 8 \text{ A}$	-		1.1	V
$t_{rr}$	Reverse recovery time	$I_{SD} = 8 \text{ A}$ , $di/dt = 100 \text{ A}/\mu\text{s}$ , $V_{DD} = 32 \text{ V}$ , $T_j = 150 \text{ }^\circ\text{C}$ (see <a href="#">Figure 15: "Test circuit for inductive load switching and diode recovery times"</a> )	-	26		ns
$Q_{rr}$	Reverse recovery charge		-	21		nC
$I_{RRM}$	Reverse recovery current		-	1.7		A

**Notes:**

<sup>(1)</sup>Pulse test: pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%



For the P-channel Power MOSFET, current polarity of voltages and current have to be reversed.

## 2.1 Electrical characteristics (curves)

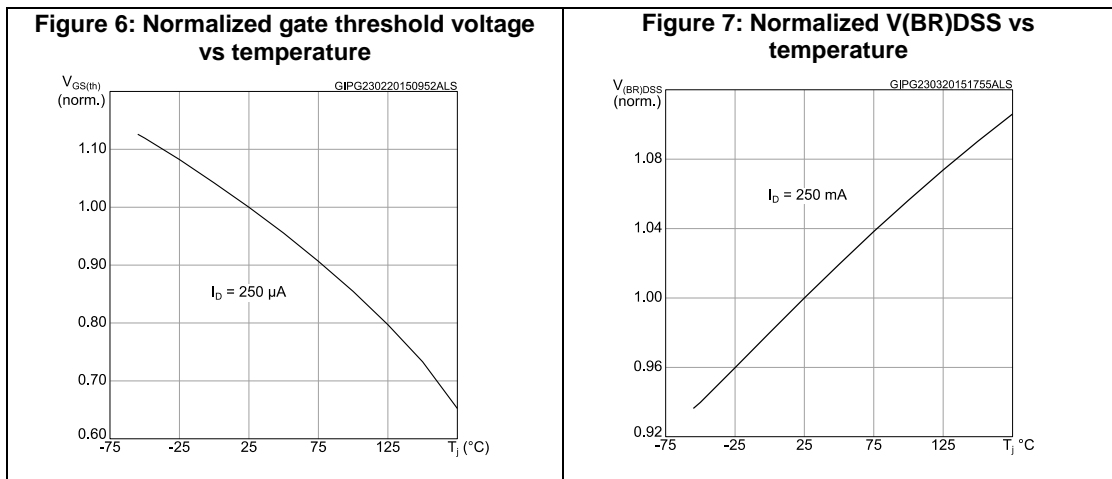
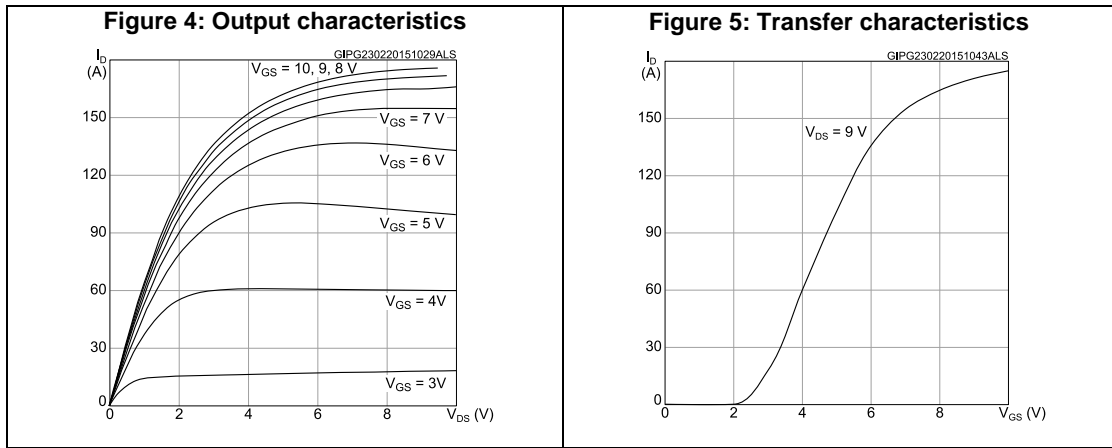
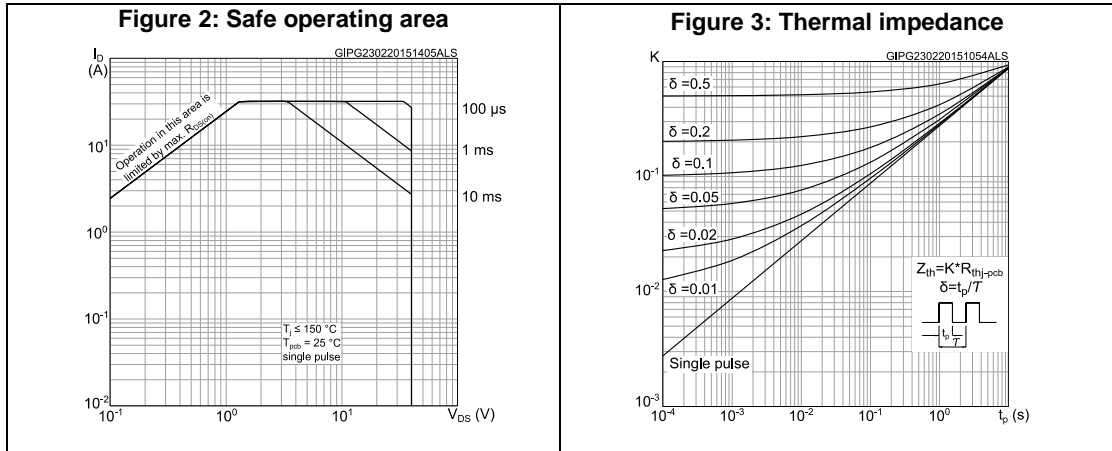


Figure 8: Static drain-source on-resistance

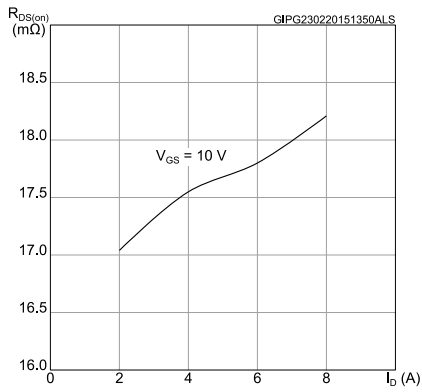


Figure 9: Normalized on-resistance vs. temperature

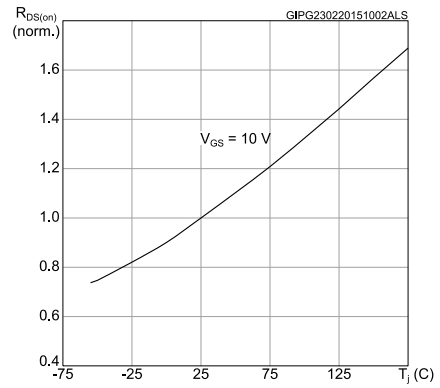


Figure 10: Gate charge vs gate-source voltage

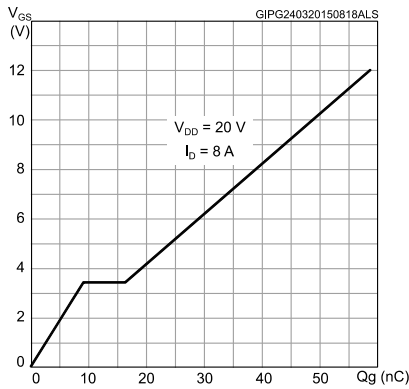


Figure 11: Capacitance variations voltage

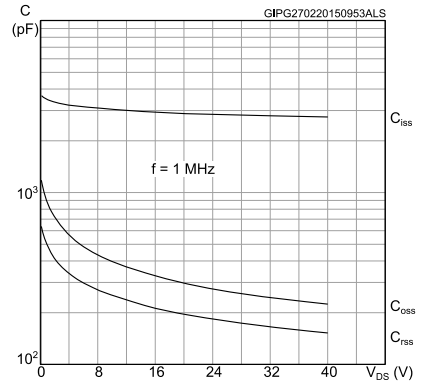
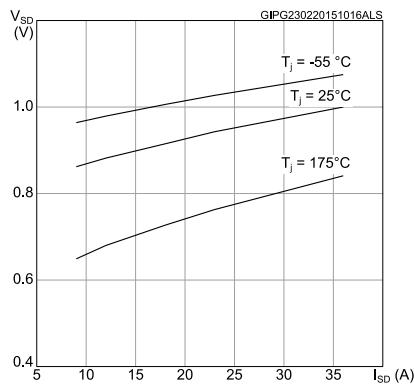


Figure 12: Source-drain diode forward characteristics



### 3 Test circuits

Figure 13: Switching times test circuit for resistive load

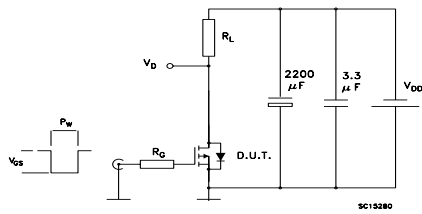


Figure 14: Gate charge test circuit

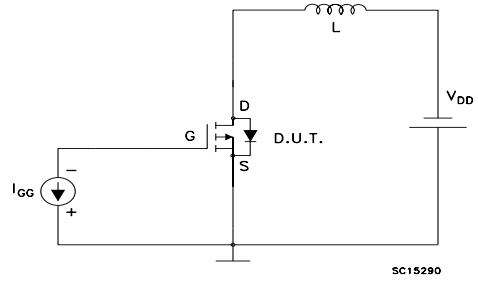
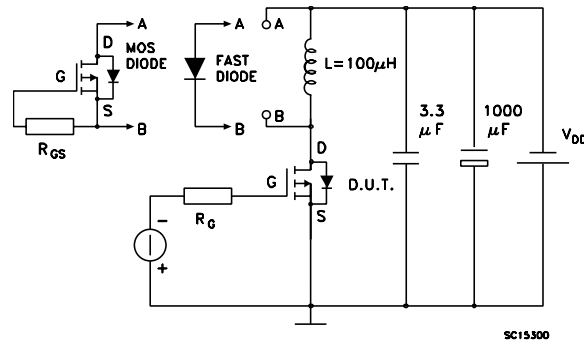


Figure 15: Test circuit for inductive load switching and diode recovery times





## 4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK<sup>®</sup> is an ST trademark.

### 4.1 PowerFLAT™ 3.3x3.3 package information

Figure 16: PowerFLAT™ 3.3x3.3 package outline

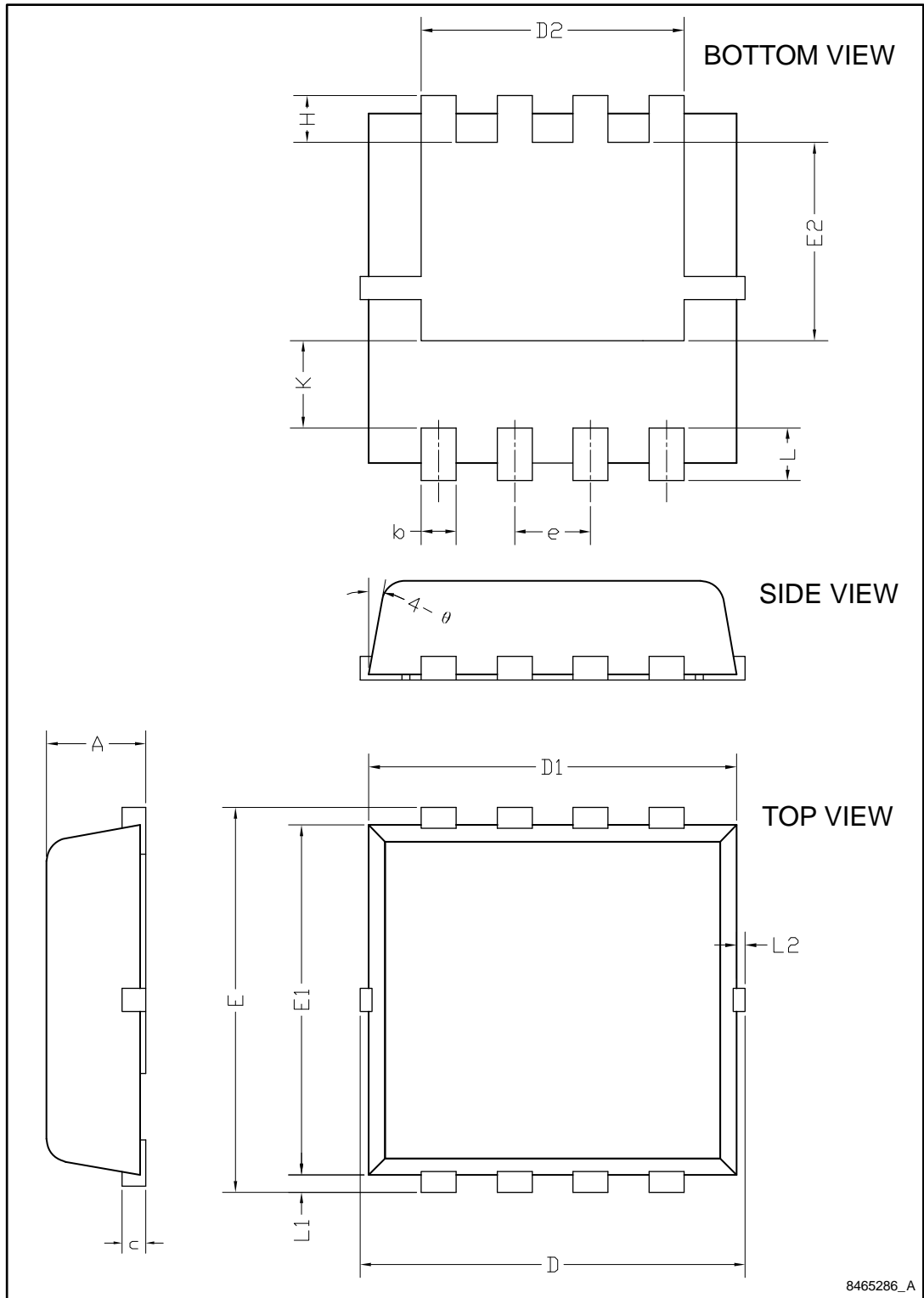
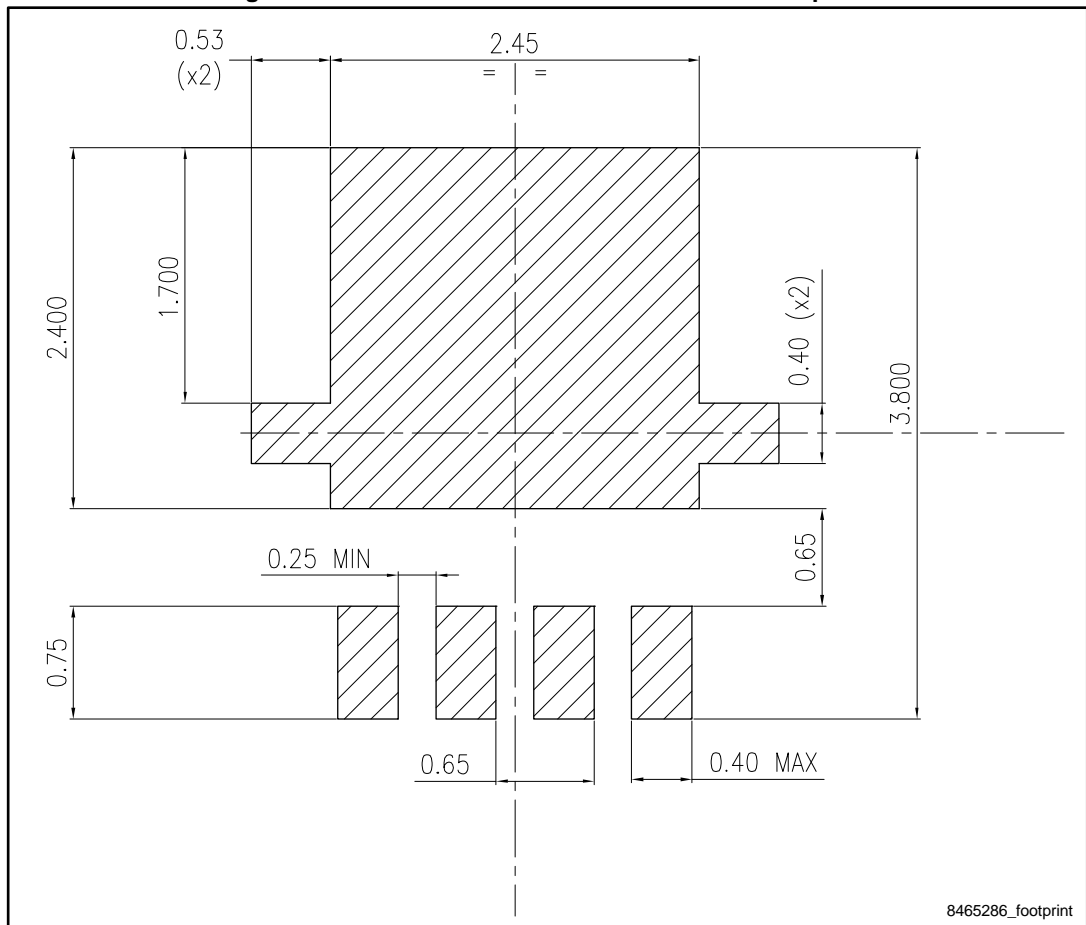


Table 8: PowerFLAT™ 3.3x3.3 mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	0.70	0.80	0.90
b	0.25	0.30	0.39
c	0.14	0.15	0.20
D	3.10	3.30	3.50
D1	3.05	3.15	3.25
D2	2.15	2.25	2.35
e	0.55	0.65	0.75
E	3.10	3.30	3.50
E1	2.90	3.00	3.10
E2	1.60	1.70	1.80
H	0.25	0.40	0.55
K	0.65	0.75	0.85
L	0.30	0.45	0.60
L1	0.05	0.15	0.25
L2			0.5
∅	8°	10°	12°

Figure 17: PowerFLAT™ 3.3x3.3 recommended footprint



## 5 Revision history

**Table 9: Document revision history**

Date	Revision	Changes
28-Jan-2014	1	Initial release.
24-Mar-2015	2	Text edits throughout document On cover page, updated title, description and features table Updated Table 4: Static Updated Table 5: Dynamic Updated Table 6: Switching times Updated Table 7: Source-drain diode Added Section 2.1: Electrical characteristics (curves) Renamed and updated Section 4.1 PowerFLAT™ 3.3 x 3.3 package information

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